



IRFP354PBF Information



For Reference Only

Part Number IRFP354PBF **Manufacturer** Vishay Siliconix

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 450V 14A TO-247AC

Package TO-247-3

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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IRFP354PBF Specifications

Manufacturer Part NumberIRFP354PBFManufacturerVishay SiliconixCategoryDiscrete Semiconductor ProductsPackageTO-247-3Series-FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)450VCurrent - Continuous Drain (Id) @ 25°C14A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs160nC @ 10VInput Capacitance (Ciss) (Max) @ Vds2700pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)190W (Tc)Rds On (Max) @ Id, Vgs350 mOhm @ 8.4A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough Hole		
Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single TO-247-3 Series TO-247-3 FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 350 mOhm @ 8.4A, 10V Operating Temperature	Manufacturer Part Number	IRFP354PBF
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Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250μA Gate Charge (Qg) (Max) @ Vgs 160nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 2700pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 190W (Tc) Rds On (Max) @ Id, Vgs 350 mOhm @ 8.4A, 10V Operating Temperature -55°C ~ 150°C (TJ)	Drain to Source Voltage (Vdss)	450V
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Input Capacitance (Ciss) (Max) @ Vds 2700pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 190W (Tc) Rds On (Max) @ Id, Vgs 350 mOhm @ 8.4A, 10V Operating Temperature -55°C ~ 150°C (TJ)	Vgs(th) (Max) @ Id	4V @ 250μA
Vgs (Max) $\pm 20 \text{V}$ FET Feature-Power Dissipation (Max) 190W (Tc) Rds On (Max) @ Id, Vgs $350 \text{ mOhm } @ 8.4 \text{A}, 10 \text{V}$ Operating Temperature $-55^{\circ}\text{C} \sim 150^{\circ}\text{C (TJ)}$	Gate Charge (Qg) (Max) @ Vgs	160nC @ 10V
FET Feature - Power Dissipation (Max) 190W (Tc) Rds On (Max) @ Id, Vgs 350 mOhm @ 8.4A, 10V Operating Temperature -55°C ~ 150°C (TJ)	Input Capacitance (Ciss) (Max) @ Vds	2700pF @ 25V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 350 mOhm @ 8.4A, 10V Operating Temperature -55°C ~ 150°C (TJ)	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs 350 mOhm @ 8.4A, 10V Operating Temperature -55°C ~ 150°C (TJ)	FET Feature	-
Operating Temperature $-55^{\circ}\text{C} \sim 150^{\circ}\text{C} \text{ (TJ)}$	Power Dissipation (Max)	190W (Tc)
	Rds On (Max) @ Id, Vgs	350 mOhm @ 8.4A, 10V
Mounting Type Through Hole	Operating Temperature	-55°C ~ 150°C (TJ)
-	Mounting Type	Through Hole
Supplier Device Package TO-247-3	Supplier Device Package	TO-247-3
Package / Case TO-247-3	Package / Case	TO-247-3
Report errors?		Report errors?

IRFP354PBF Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

IRFP354PBF Payment Methods



















IRFP354PBF Shipping Methods













If you have any question about IRFP354PBF, please do not hesitate to contact us!

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